

# Proximity-induced superconducting gap in the quantum spin Hall edge state of monolayer WTe<sub>2</sub>

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**The quantum spin Hall (QSH) state was recently demonstrated in monolayers of the transition metal dichalcogenide 1T'-WTe<sub>2</sub> and is characterized by a band gap in the two-dimensional (2D) interior and helical one-dimensional (1D) edge states [1–3]. Inducing superconductivity in the helical edge states would result in a 1D topological superconductor, a highly sought-after state of matter [4]. In the present study, we use a novel dry-transfer flip technique to place atomically-thin layers of WTe<sub>2</sub> on a van der Waals superconductor, NbSe<sub>2</sub>. Using scanning tunneling microscopy and spectroscopy (STM/STS), we demonstrate atomically clean surfaces and interfaces and the presence of a proximity-induced superconducting gap in the WTe<sub>2</sub> for thicknesses from a monolayer up to 7 crystalline layers. At the edge of the WTe<sub>2</sub> monolayer, we show that the superconducting gap coexists with the characteristic spectroscopic signature of the QSH edge state. Taken together, these observations provide conclusive evidence for proximity-induced superconductivity in the QSH edge state in WTe<sub>2</sub>, a crucial step towards realizing 1D topological superconductivity in this van der Waals material platform.**

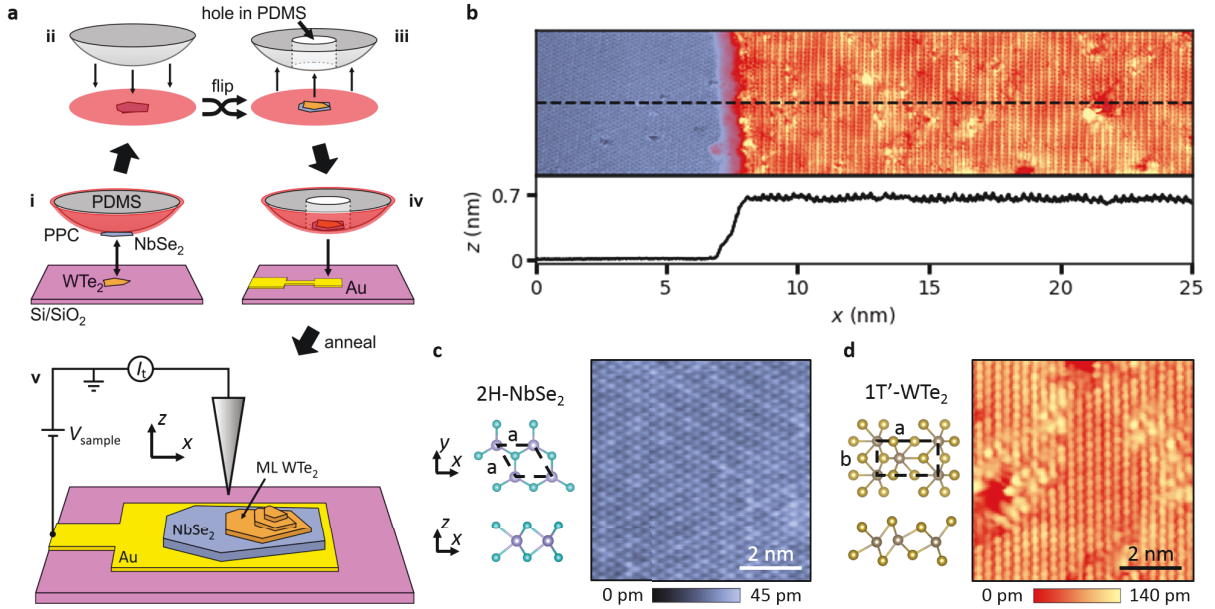
A topological superconductor is a state of matter classified by a pairing gap that gives rise to protected gapless excitations at its boundaries. Contemporary interest in topological superconductors has been driven by these gapless excitations, thought to be emergent Majorana quasiparticles with non-abelian statistics [5–8]. One path toward topological superconductivity is to realize an intrinsic spinless  $p$ -wave superconductor [9]. A powerful alternative is by using a conventional  $s$ -wave superconductor to induce Cooper pairing in topologically non-trivial states via the superconducting proximity effect, resulting in an effective  $p$ -wave pairing [10]. This approach has been employed to engineer 2D topological superconductivity in epitaxial topological insulator films grown on a superconducting substrate [11, 12], and 1D topological superconductivity by proximitizing a quantum spin Hall (QSH) state in buried epitaxial semiconductor quantum wells [13, 14]. While such demonstrations mark important milestones, there are clear advantages for exploring topological superconductivity in the van der Waals material platform. Using layered 2D materials allows the 2D QSH edge to be proximitized in vertical heterostructures, circumventing the length restrictions of lateral proximity-effect geometries. Furthermore, the surfaces and edges are readily available for surface probes,

allowing detection and fundamental study of signatures of the topological superconducting state.

Following recent theoretical predictions [15], an intrinsic QSH state was demonstrated in a monolayer (ML) of 1T'-WTe<sub>2</sub> [1–3, 16–18]. WTe<sub>2</sub> is attractive for studying the QSH edge modes because it can be readily incorporated in van der Waals heterostructures and has shown quantized edge conductance up to 100 K [3]. Furthermore, ML WTe<sub>2</sub> was recently also shown to host intrinsic superconducting behavior below  $\sim 1$  K when electrostatically gated into the conduction band [19, 20].

In the present work, we study mechanically-exfoliated single- and few-layers of WTe<sub>2</sub> which have been transferred onto a van der Waals  $s$ -wave superconductor, NbSe<sub>2</sub>. We show that this approach induces a superconducting gap in the WTe<sub>2</sub> without the need for electrostatic doping and yields a critical temperature much higher than that of the intrinsic WTe<sub>2</sub> superconductivity, an experimental advantage which greatly facilitates studies of the interplay of superconductivity and the QSH edge modes. We employ scanning tunneling microscopy and spectroscopy (STM/STS) to investigate the proximity-induced superconducting gap as a function of temperature, magnetic field, and WTe<sub>2</sub> thickness. By spatially resolving the spectroscopic features of the WTe<sub>2</sub>, we find that the superconducting gap coexists with the QSH signature at the ML WTe<sub>2</sub> edge, demonstrating critical steps toward identifying 1D topological superconductivity in a van der Waals material system.

We have developed a novel fabrication technique which enables the assembly and deterministic placement of van der Waals heterostructures (Fig. 1a). Though similar methods have been used to fabricate complex encapsulated mesoscale devices [21], critically, our technique produces atomically-clean surfaces of air-sensitive materials suitable for scanning probe measurements. Figure 1b shows an STM image of a heterostructure where the WTe<sub>2</sub> ML edge and the underlying NbSe<sub>2</sub> are visible, showing atomically-clean surfaces on each material. The height profile across the step edge gives a step height of  $\sim 7$  Å which corresponds to one WTe<sub>2</sub> layer [17], indicating an atomically-clean interface between the WTe<sub>2</sub> and NbSe<sub>2</sub>. Atomically-resolved STM images of the NbSe<sub>2</sub> surface (Fig. 1c) show the well-known  $3 \times 3$  charge density wave [11], indicating the pristine quality of the NbSe<sub>2</sub> substrate. Atomically-resolved STM images of the WTe<sub>2</sub> ML (Fig. 1d) are characterized by vertical atomic rows parallel to the  $b$ -axis



**FIG. 1. Fabrication and morphology of  $\text{WTe}_2/\text{NbSe}_2$  heterostructure.** (a) Schematic of the sample fabrication. After assembly of the  $\text{NbSe}_2/\text{WTe}_2$  heterostructure using a PPC/PDMS stamp (inside a nitrogen-filled glove box), the PPC film is peeled off, flipped upside down and put onto a new PDMS stamp which has a hole in it. This stamp is used to deterministically place the heterostructure onto pre-patterned gold leads without bringing the heterostructure surface into contact with any polymers or solvents. The PPC is then evaporated by annealing under vacuum conditions and the sample is transferred to the STM, all without intermediate air-exposure. (b) STM topography and height profile across the edge of the monolayer  $\text{WTe}_2$  flake ( $V_{\text{sample}} = 300$  mV and  $I_t = 10$  pA). (c) Atomic structures and atomically-resolved STM image of the  $\text{NbSe}_2$  flake showing the  $3 \times 3$  CDW ( $V_{\text{sample}} = 300$  mV and  $I_t = 35$  pA). (d) Atomic structures and atomically-resolved STM image of ML  $\text{WTe}_2$  ( $V_{\text{sample}} = 1$  V and  $I_t = 55$  pA). In (b) a moiré pattern in the form of diagonal stripes can be seen on the ML  $\text{WTe}_2$  resulting from the superposition of the two different atomic lattices. While  $\text{NbSe}_2$  has a hexagonal unit cell with lattice parameters  $a = b = 3.44$  Å,  $\text{WTe}_2$  has a rectangular unit cell with lattice parameters  $a = 6.28$  Å and  $b = 3.48$  Å (Fig. 1c, d). The moiré pattern, analyzed in more detail in the SI, corresponds to a twist angle of  $\approx 3^\circ$ . The topographies shown in (b), (c), and (d) are representative of the heterostructure over most of the area of the exfoliated flakes.

of the  $\text{WTe}_2$  unit cell. Turning now to spectroscopic analysis of these surfaces, Fig. 2a shows a map of  $dI/dV$  spectra taken along a line perpendicular to the  $\text{WTe}_2$  monolayer step edge (upper panel) and the corresponding height profile (lower panel). The  $dI/dV$  spectra clearly show the presence of an increased local density of states (LDOS) near the  $\text{WTe}_2$  step edge. This feature was recently reported in STM/STS studies of ML films of  $\text{WTe}_2$  grown on epitaxial graphene substrates [1, 16]. Based on combined evidence from ARPES and STS in Ref. 1, it was concluded that ML  $\text{WTe}_2$  has a band gap of  $(56 \pm 14)$  meV, and that the increased LDOS at the ML  $\text{WTe}_2$  edge signifies the metallic QSH edge state. In our monolayer samples, produced via isolation from bulk crystals rather than molecular beam epitaxy, and on superconducting substrates rather than graphene, we observe the same spectroscopic features, which we attribute to the same QSH edge state. Figure 2b shows the averaged  $dI/dV$  spectrum on the  $\text{WTe}_2$  ML (red) and the ML edge (orange) at the corresponding positions indicated in Fig. 2a. The spectroscopic signature of the QSH edge state is evident primarily in the valence band but, importantly, the edge state also crosses the band gap. Following the interpretation of Ref. 1, the increases in the  $dI/dV$  signal at  $E - E_F \approx -50$  meV and  $E - E_F \approx 15$  meV corre-

spond to the onset of the  $\text{WTe}_2$  valence and conduction band, respectively, locating  $E_F$  in the ML  $\text{WTe}_2$  band gap. A non-zero  $dI/dV$  signal in the band gap away from the step edge was proposed to be due to defect states and substrate effects [1]. In addition, tip-induced band bending may play a role in introducing spectral weight in the  $\text{WTe}_2$  band gap (see Supplementary Information (SI)). By comparing the positions of the observed spectral features to epitaxially-grown  $\text{WTe}_2$  on graphene [1, 16] and exfoliated  $\text{WTe}_2$  [22], we conclude that there is no significant charge transfer from the  $\text{NbSe}_2$  to the  $\text{WTe}_2$ . This observation is further supported by our density functional theory (DFT) calculations of the ML  $\text{WTe}_2/\text{NbSe}_2$  heterostructure, which show no significant modification of the  $\text{WTe}_2$  electronic structure compared to a freestanding ML of  $\text{WTe}_2$  (see SI).

Measurements of the ML  $\text{WTe}_2$   $dI/dV$  spectrum over a smaller voltage range (Fig. 2c), reveal a new feature: a superconducting gap-like feature centered around the Fermi energy, characterized by a dip in the  $dI/dV$  signal with peaks on either side of the gap. Comparison of measurements at 4.7 K and 2.8 K show that the gap deepens and the peaks sharpen at lower temperature. The evolution of the superconducting gap-like feature under application of a surface-normal mag-

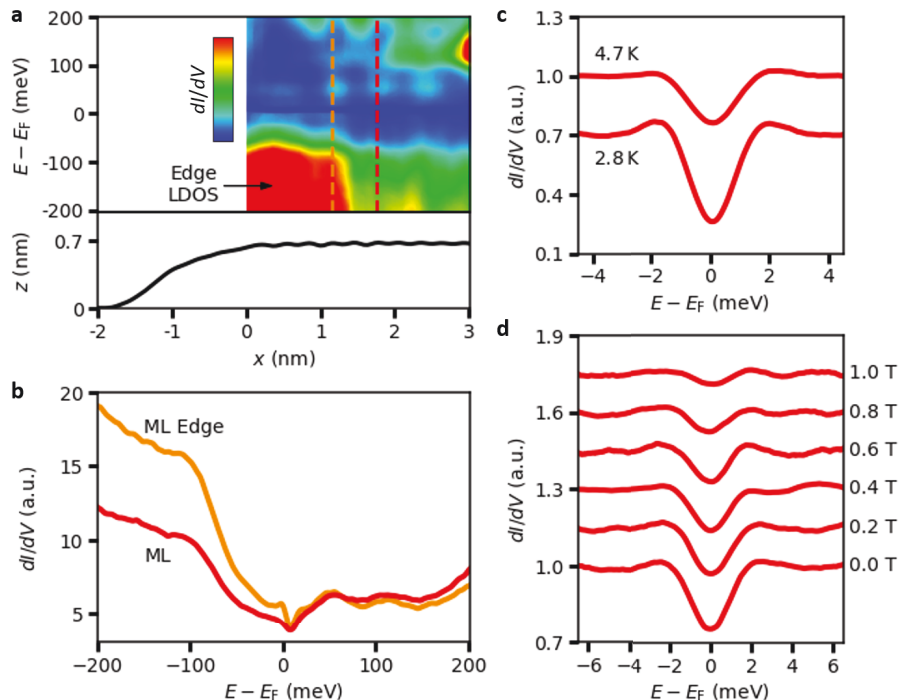


FIG. 2. **Simultaneous presence of quantum spin Hall edge state and superconducting gap in monolayer WTe<sub>2</sub>.** (a)  $dI/dV$  spectra taken along a line across the step edge of the WTe<sub>2</sub> flake (top), and corresponding height profile (bottom) ( $V_{\text{sample}} = 300$  mV and  $I_t = 400$  pA). (b) Spatially averaged  $dI/dV$  spectra of monolayer WTe<sub>2</sub> showing a representative spectrum away from the monolayer edge (corresponding to the red dashed line in a) and increased density of states at the monolayer edge due to presence of the QSH edge state (corresponding to orange dashed line in a). Small voltage range  $dI/dV$  spectrum of monolayer WTe<sub>2</sub> at 4.7 K and 2.8 K showing superconducting gap-like features. The 2.8 K curve is offset for clarity. (d) Magnetic field dependence of the small voltage spectrum of monolayer WTe<sub>2</sub> measured at 4.7 K. The curves are offset for clarity.

netic field at 4.7 K (Fig. 2d) shows that with increasing magnetic field, the gap becomes less deep and the peaks flatten out until the gap features have nearly vanished at 1 T. To understand this gap, we fit the observed superconducting-like gap with the Bardeen-Cooper-Schrieffer (BCS) spectrum (see SI). We find that the BCS model fits both the monolayer WTe<sub>2</sub> and the NbSe<sub>2</sub> data well (Fig. 3a). For NbSe<sub>2</sub>, the fit results in a superconducting gap of  $\Delta_{\text{NbSe}_2} = (0.84 \pm 0.01)$  meV, while for the WTe<sub>2</sub> it results  $\Delta_{\text{WTe}_2} = (0.72 \pm 0.02)$  meV. In addition to following the trend of a superconducting gap with applied magnetic field, the vanishing of the gap near 1 T also agrees with the Ginzburg-Landau estimate for the upper critical field of bulk NbSe<sub>2</sub> [23]. We conclude that the gap feature observed on the ML WTe<sub>2</sub> is indeed a superconducting gap.

In order to confirm the proximity-induced nature of the observed superconducting gap, we explore its evolution as a function of WTe<sub>2</sub> thickness. The exfoliation procedure naturally produces terraces of varying thickness in our samples, enabling thickness-dependent gap measurement within a single sample. Figure 3b shows the superconducting gap measured on terraces of different numbers of WTe<sub>2</sub> layers  $N$ , revealing that the gap decreases with increasing  $N$ , as expected for decaying superconducting correlations near the boundary of a superconducting-metal interface [24]. To quantify this

behavior, we fit the BCS model to each of the spectra in Fig. 3b and plot the extracted gap sizes as filled circles in Fig. 3c. In the thick limit ( $N \geq 3$ ), we find that observed behavior shows excellent agreement with transport measurements of proximity-induced superconductivity in bulk WTe<sub>2</sub> flakes [24, 25], extending the previous studies to the ultra-thin limit (see SI). For  $N < 3$ , we observe a more rapid decrease of the extracted gap which may be explained by the strong dependence of the electronic structure of the WTe<sub>2</sub> in this thickness range, resulting in a larger mismatch of the WTe<sub>2</sub> and NbSe<sub>2</sub> Fermi surfaces and therefore a stronger dependence of the induced gap on  $N$  [26].

For monolayer and bilayer WTe<sub>2</sub>/NbSe<sub>2</sub>, we also consider the possibility that the spectra may be a superposition of tunneling into WTe<sub>2</sub> and into NbSe<sub>2</sub> (Fig. 4a,b inset). We therefore performed a control experiment, tunneling into ML WTe<sub>2</sub> on a  $\sim 20$  nm thick hBN substrate, in order to isolate the relative contributions (Fig. 4a,b). This allows us to perform a more detailed analysis of the ML WTe<sub>2</sub>/NbSe<sub>2</sub> spectrum (Fig. 4d) in which we fit a superposition of BCS spectra, with a 14% fractional contribution from ML WTe<sub>2</sub>. The resulting induced gap size is  $\Delta_{\text{WTe}_2}^{(ML)} = 0.76 \pm 0.16$  meV at 4.7 K and  $0.83 \pm 0.08$  meV at 2.8 K (Fig. 4d). For the bilayer, we find a fractional contribution of 75% and an induced gap

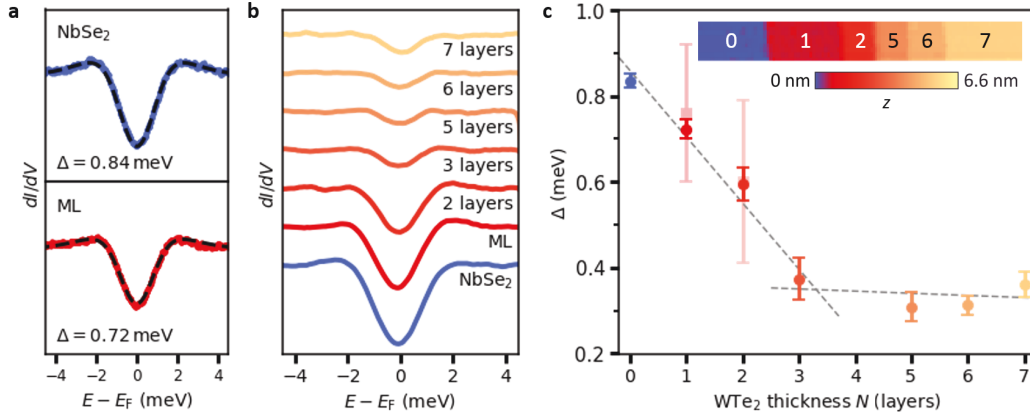


FIG. 3. **Evolution of the superconducting gap with WTe<sub>2</sub> thickness at 4.7 K.** (a) Fits of the BCS model to the superconducting gap spectra measured on NbSe<sub>2</sub> and monolayer WTe<sub>2</sub> result in  $\Delta_{\text{NbSe}_2} = (0.84 \pm 0.01)$  meV and  $\Delta_{\text{WTe}_2} = (0.72 \pm 0.02)$  meV. (b) Measurement of the superconducting gap spectrum for WTe<sub>2</sub> layer thicknesses up to 7 layers. (c) (filled circles) WTe<sub>2</sub> thickness dependence of the superconducting gap size obtained from fitting the spectra in (b) with the BCS gap equation. (filled squares) Fits of the monolayer and bilayer spectrum with a more detailed model which includes partial tunneling into the NbSe<sub>2</sub> substrate. The dashed lines indicate two different regimes in which  $\Delta$  decreases more rapidly for  $N < 3$  and more gradually for  $N \geq 3$ . The inset shows a large-scale topography image of the WTe<sub>2</sub>, where terraces of different WTe<sub>2</sub> thicknesses are observed. Scan size: 200 nm  $\times$  14 nm. The corresponding number of WTe<sub>2</sub> layers  $N$  is indicated for each terrace, where  $N = 0$  is the bare NbSe<sub>2</sub>.

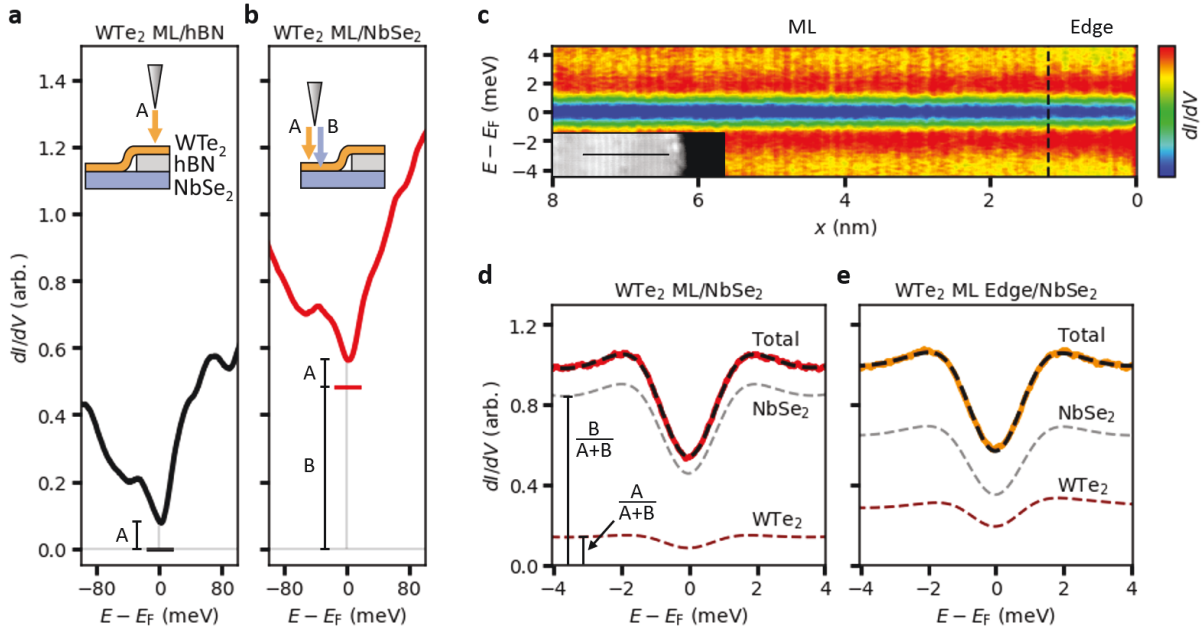


FIG. 4. **Proximity-induced superconducting gap in the quantum spin Hall edge state of monolayer WTe<sub>2</sub> at 2.8 K.** (a) Tunneling spectrum of WTe<sub>2</sub> on hexagonal boron nitride (hBN) and (b) spectrum of the *same* WTe<sub>2</sub> flake on NbSe<sub>2</sub> (for optical micrograph of the heterostructure see SI). The tunneling contributions of the WTe<sub>2</sub> and NbSe<sub>2</sub> are indicated as A and B, respectively. (c) SC gap spectra measured along a line perpendicular to the edge of the WTe<sub>2</sub>. The inset shows the topography and line along which the spectra were taken. Scan size: 16 nm  $\times$  4 nm. (d) Fitting of representative ML WTe<sub>2</sub>/NbSe<sub>2</sub> tunneling spectrum. The fractional contribution of tunneling into WTe<sub>2</sub> is  $f_{\text{WTe}_2} \equiv A/(A+B) = 0.14 \pm 0.04$ . The NbSe<sub>2</sub>-derived states contribution is therefore  $f_{\text{NbSe}_2} = B/(A+B) = 0.86 \pm 0.04$ . The model used to fit the data is  $(dI/dV)_{\text{Total}} = f_{\text{WTe}_2} \cdot (dI/dV)_{\text{WTe}_2} + f_{\text{NbSe}_2} \cdot (dI/dV)_{\text{NbSe}_2}$ , using a BCS form for each  $dI/dV$  (details in SI). The grey and maroon dashed lines indicate the  $(dI/dV)_{\text{NbSe}_2}$  and  $(dI/dV)_{\text{WTe}_2}$ , the proximity-induced SC gap in the WTe<sub>2</sub>. The size of the induced gap is  $\Delta_{\text{WTe}_2}^{(\text{ML})} = 0.83 \pm 0.08$  meV. (e) Fitting of the ML edge WTe<sub>2</sub>/NbSe<sub>2</sub> tunneling spectrum. We use the same gap(s) found for NbSe<sub>2</sub> from (a) and use  $\Delta_{\text{WTe}_2}^{(\text{edge})}$  and the new fractional contribution of the WTe<sub>2</sub> edge state,  $f_{\text{WTe}_2}^{(\text{edge})}$  as fitting parameters (details in SI). The resulting induced SC gap in the WTe<sub>2</sub> QSH edge state is  $\Delta_{\text{WTe}_2}^{(\text{edge})} = 0.75 \pm 0.08$  meV.

of  $\Delta_{\text{WTe}_2}^{(BL)} = 0.60 \pm 0.19$  meV. In Fig. 3c we plot the 4.7 K induced gaps and find no significant deviation from those determined by the one-gap fits.

Finally, we consider the lateral variation of the superconducting gap from within the ML WTe<sub>2</sub> to the region occupied by the edge state. Figure 4c shows  $dI/dV$  spectra taken at 2.8 K along a line approaching the physical edge of the WTe<sub>2</sub> monolayer, similar to that shown in Fig. 2a but over a smaller voltage range. The superconducting gap is present throughout the WTe<sub>2</sub> monolayer with only slight changes in the gap width and depth. It is apparent that a superconducting gap is present in the region in which the QSH edge state is observed in Fig. 2a (indicated by the dashed line in Fig. 4c). To confirm that there is a fractional contribution to this spectrum due to an induced gap in the QSH edge state, in Fig. 4e we perform a similar fit as we did for the spectrum 10 nm away from the edge in Fig. 4d. We find that the induced gap in the edge state has a value of  $\Delta_{\text{WTe}_2}^{(edge)} = 0.75 \pm 0.08$  meV. The observation of a gap in the edge state of monolayer 1T'-WTe<sub>2</sub> provides strong evidence that we have created a 1D topological insulator in a van der Waals heterostructure by proximity-induced superconductivity in the quantum spin Hall edge state.

The topological nature of a superconducting QSH edge state could be explicitly demonstrated in an STM measurement by creating a boundary with a portion of the same QSH edge state in which a topologically-trivial gap has been opened [4]. This would localize Majorana zero modes at the boundary, which can be identified as a zero-bias conductance peak within the superconducting gap [27]. Creating such a boundary is straightforward in the van der Waals material platform, e.g., by integrating a van der Waals magnetic insulator into the heterostructure shown in Fig. 1a to open a local Zeeman gap. Our work establishes the groundwork for such an experiment with a clear path toward the realization of Majorana quasiparticles. In addition, the method of sample preparation outlined in this work may be easily adapted to numerous experiments involving surface-probe studies or air-sensitive materials.

## METHODS

WTe<sub>2</sub> and NbSe<sub>2</sub> were exfoliated onto SiO<sub>2</sub> in a nitrogen-filled glovebox. A WTe<sub>2</sub> flake with regions of different thicknesses was transferred onto a  $(20 \pm 1)$  nm thick NbSe<sub>2</sub> flake using the technique depicted in Fig. 1a. At this thickness, the electronic properties of the NbSe<sub>2</sub> are bulk-like and the critical temperature below which the NbSe<sub>2</sub> becomes superconducting is  $T_c \approx 7$  K [28]. For optical images of the sample and further details on the sample fabrication see SI. The STM tip is approached to the WTe<sub>2</sub>/NbSe<sub>2</sub> heterostructure using a capacitive technique adapted from Ref. [29]. The commercial CreaTec STM helium bath temperature is 4.2 K with the ability of intermittently reaching  $\sim 1$  K by pumping on the cryostat. The resulting STM temperatures are 4.7 K and 2.8 K, respectively, due to vibration isolation and opti-

cal access. The STM is equipped with an electrochemically-etched tungsten tip which was indented into gold prior to and in between measurements. The lock-in frequency was set to  $f = 925$  Hz in all  $dI/dV$  measurements. All superconducting gap measurements were performed at  $V_{\text{sample}} = 5$  mV with  $V_{\text{mod}} = 100$   $\mu$ V peak-to-peak and  $I_t = 100$  pA, except in Fig. 2 e) where  $V_{\text{sample}} = 10$  mV. The spectra in Fig. 2 a) and b) were acquired using  $V_{\text{mod}} = 5$  mV. In Fig. 4, tunneling parameters are:  $V_{\text{sample}} = 300$  mV,  $I_t = 100$  pA and  $V_{\text{mod}} = 5$  mV in (a) and  $V_{\text{sample}} = 300$  mV,  $I_t = 110$  pA and  $V_{\text{mod}} = 10$  mV in (b). For quantitative comparison, the two spectra were normalized to the tunneling current and  $V_{\text{mod}}$ .

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## AUTHOR CONTRIBUTIONS

F.L., D.W., R.M.F. and B.M.H. designed the experiment. F.L. and D.W. acquired the experimental data and F.L., D.W., and R.M.F. analyzed the data and performed the fitting to the spectra. F.L., D.W. and S.C.d.l.B. fabricated the samples. F.L., D.W., S.C.d.l.B. and B.M.H. wrote the manuscript, and all authors commented on the manuscript. J.Y. grew the WTe<sub>2</sub> crystals. D.M. provided other van der Waals crystals used in this study. M.W. performed DFT calculations. R.M.F. and B.M.H. supervised the project.

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